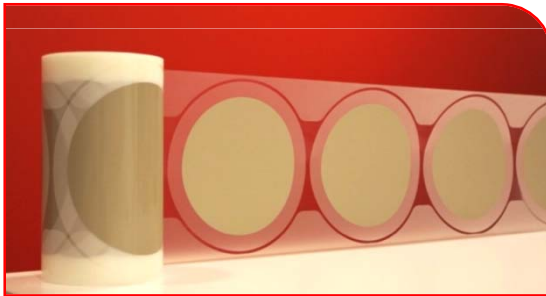




# Conductive Die Attach Film - CDAF

Higher Reliability Conductive Die Attach Films:  
Compatible with Si and GaAs Wafers

*MEPTEC Luncheon – December 11<sup>th</sup> 2013*



Presented by Shashi Gupta



# Contents

1. Market & Package Trend
2. Current Material Challenges & Needs
3. cDAF Technology
4. Bulk vs In-package measurements
5. Product Roadmap
6. cDAF on GaAs wafer technology
7. cDAF Advantages
8. Summary

# Market Trends

Smaller, Faster, Higher Functionalities



- Higher density design
- Higher functionalities
- Faster signal speed
- Power Management
- Lower TCoO
- Reduce package thickness

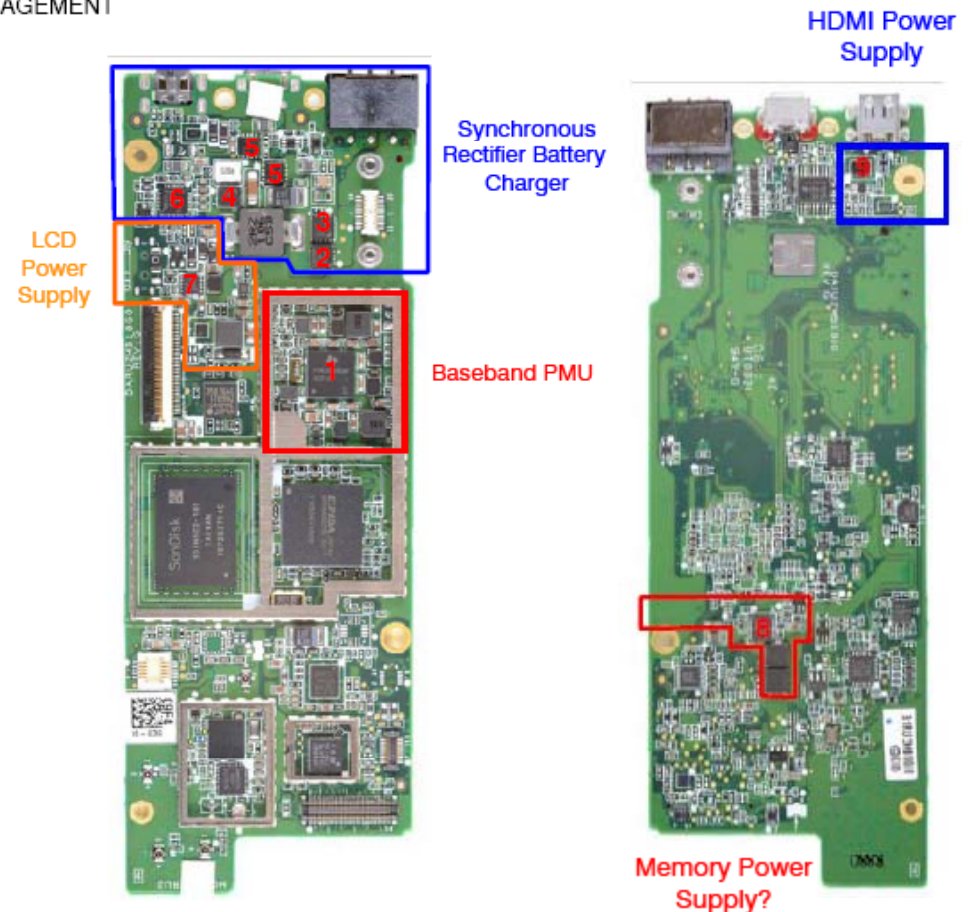
Applications space covers consumer, mobile, computing, communication health care, energy, industrial and automotive.

# Market Trends

## An Example – Source Prismark

### RIM PLAYBOOK POWER MANAGEMENT

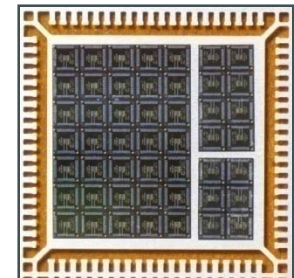
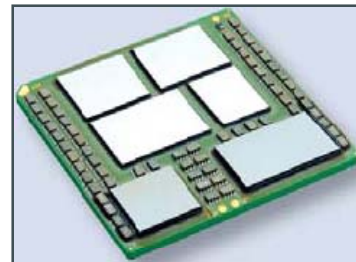
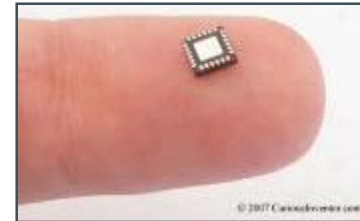
1. Texas Instruments TWL6030 Power Manager
  - 256-CSP
2. TI/CICLON CSD25401 P-Channel NexFET Power MOSFET
  - QFN3.3x3.3
3. Fairchild FDMC510P P-Channel PowerTrench MOSFET
  - QFN 3.3x3.3
4. Fairchild FDMC7200 Power Trench MOSFET “non catalogue”
5. Alpha and Omega AON740130V P-Channel MOSFET
  - DFN 3x3mm
6. Intersil ISL9519 Highly Integrated Narrow VDC System Voltage Regulator and Battery Charger controller
  - QFP-28
7. Texas Instruments TPS63031 High Efficient Single Inductor Buck-Boost Converter w/1-A Switches
  - QFN-10
8. Texas Instruments PS63020 High Efficiency Single Inductor Buck-Boost Converter with 4A Switch
  - QFN-14
9. Texas Instruments TPD12SO15YFFR HDMI Companion Chip with Step-up Converter, 12C Level Shifter, and High-speed ESD Clamps
  - WSCSP-28



# Package Trends - Wirebonded

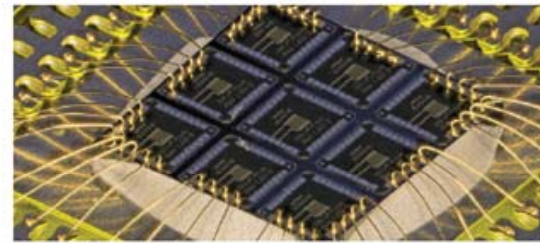
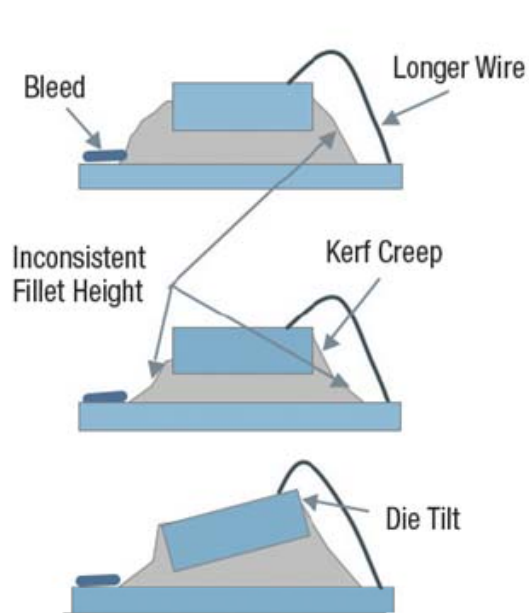
## Higher Functionality & Efficiency

- Miniaturized packages (QFN, DFN, SOs)
  - Increased die-to-pad ratio
  - In some case D/P ratio close to 1.0
- Thinner packages (QFN, SO, QFP)
  - Packages  $<0.3\text{mm}$
  - Thinner die  $<75\mu\text{m}$
  - Thinner DA bondline thickness  $<20\mu\text{m}$
- Higher density packages
  - Multi-dies packages
    - SiP – LGA/PBGA

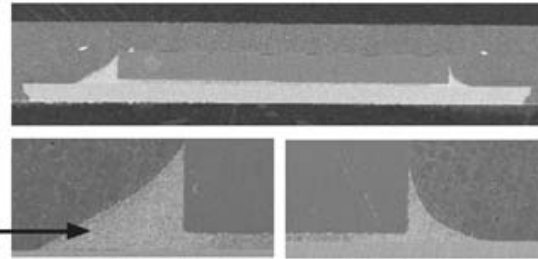


# Current Material Challenges on LFs

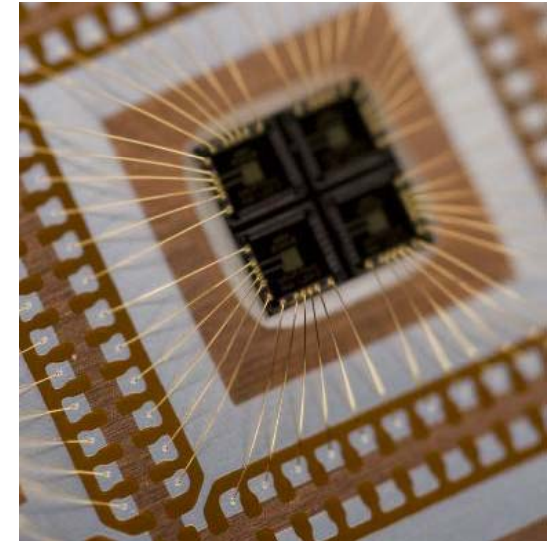
## Conducting Die Attach Paste



Typical paste-based die attach.



Cross section of typical paste die attach.



- **Dispensing:** Optimize dispense patterns for various die sizes - 0.2 x0.2 mm to >10x10mm.
- **Fillet & Bleed:** Forces engineers to have a minimum keep out zone around die
- **Bondline Control:** Specially for smaller die BLT control is challenging and leads to die tilt
- **Kerf creep:** For thinner wafers uneven fillet height can lead to kerf creep

# Future Material Needs

What does the market really need moving forward ?

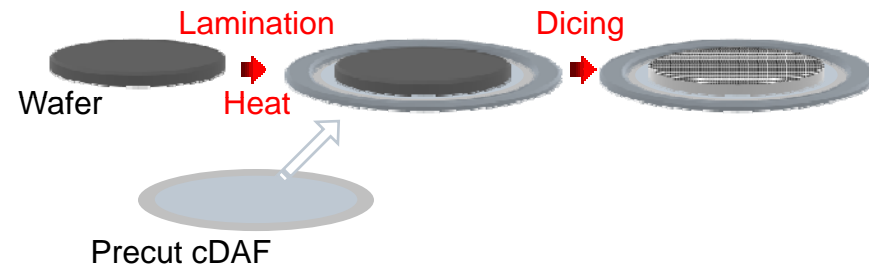
- Lower Cost
- Higher Reliability
- Zero Delamination
- Zero Bleed
- Minimal fillet
- Consistent BLT control
- Thin Wafer handling capability
- Low to no outgassing
- Drop in solution

# New Materials – Conductive Die Attach Films

Controlled flow technology



Lamination Process:



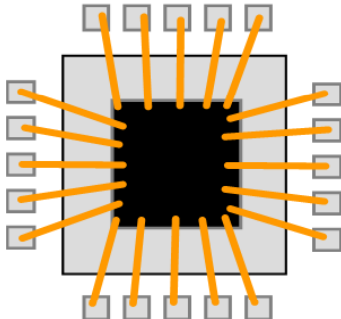
Precut conductive die attach films offer a single step lamination to wafer back



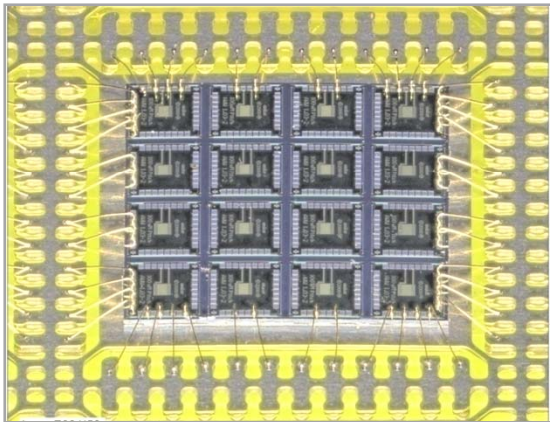
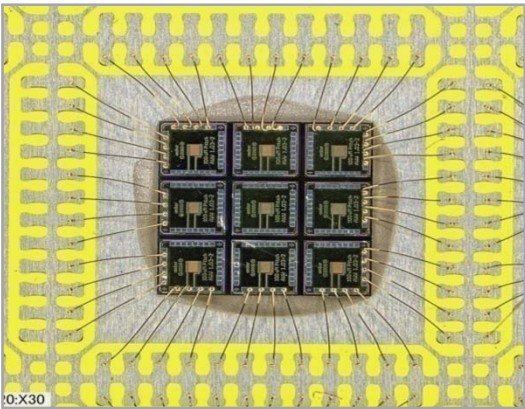
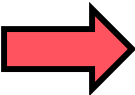
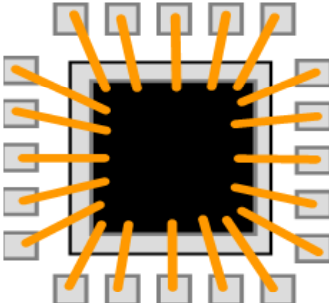
# Control Flow

Enables Miniaturization

With Fillet



Controlled Fillet



Reduced footprint



Shorter interconnection



Faster signal speed

Less Au wire, leadframe, EMC used



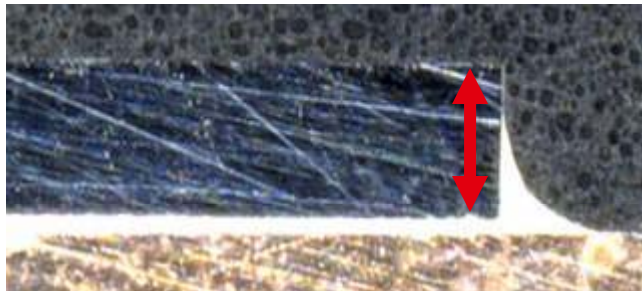
Lower TCoO



# Control Flow

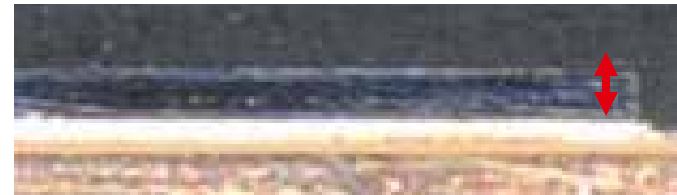
## Thin Wafer Handling

Package with Fillet



Die Attach Paste

Controlled Fillet Height



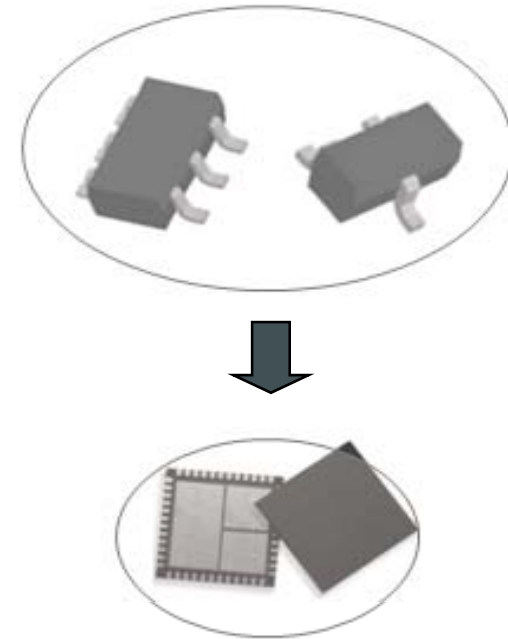
Die Attach Film

- Thinner wafer handling enabled
- Consistent Thinner bondlines achieved
  - Eliminated Fillet
  - Eliminated bleed

# Advantages of Control Flow

## Package level

- **Enables emerging packages:**
  - Miniaturized
  - High density
  - Ultra thin
- **Indirectly improves package performance:**
  - Faster signal speed (shorter interconnection)
  - Better power management (low RdSon)
  - Better heat dissipation
- **Indirectly reduces TCoO:**
  - Cheaper design choice (SiP vs. SoC)
  - Less material used (high packaging density)
  - Improve yield

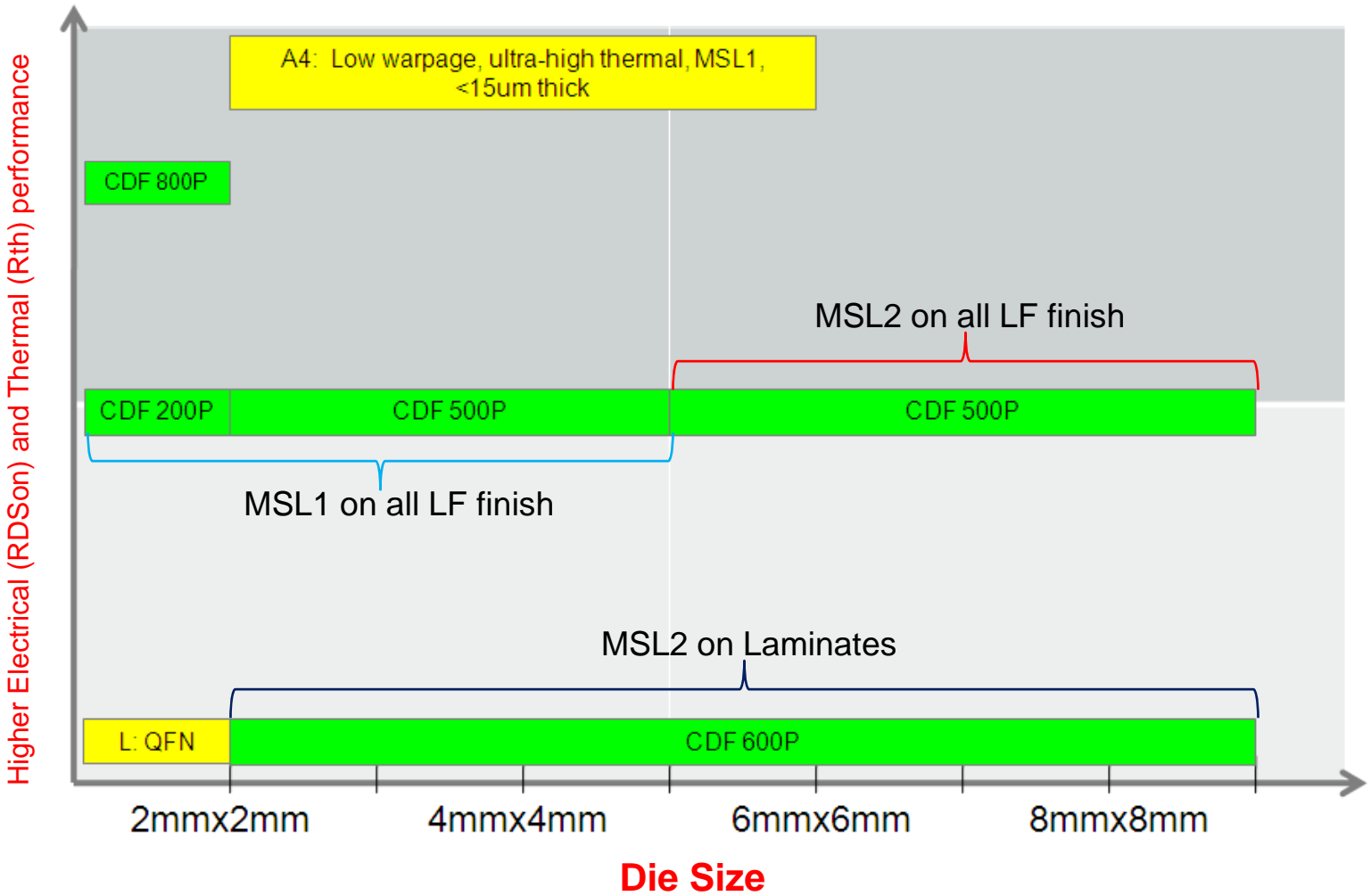


Footprint reduction (>50%):  
Multiple packages to one  
using multiple die.

**CDAF technology is well-aligned with emerging package trends**

# Henkel's Solution to Control Flow

## Product Space



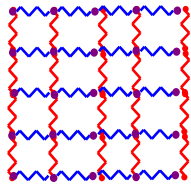
# Why CDAF has higher reliability

## Paste and Film comparison

### Paste material

Low viscosity

Thermoset monomer with lower molecular weight



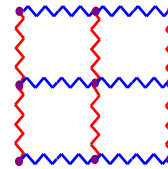
High cross-linking density  
Low toughness

Lower adhesion  
Inferior MSL performance

### Film material

High viscosity

Thermoset monomer with higher molecular weight (solid resins)

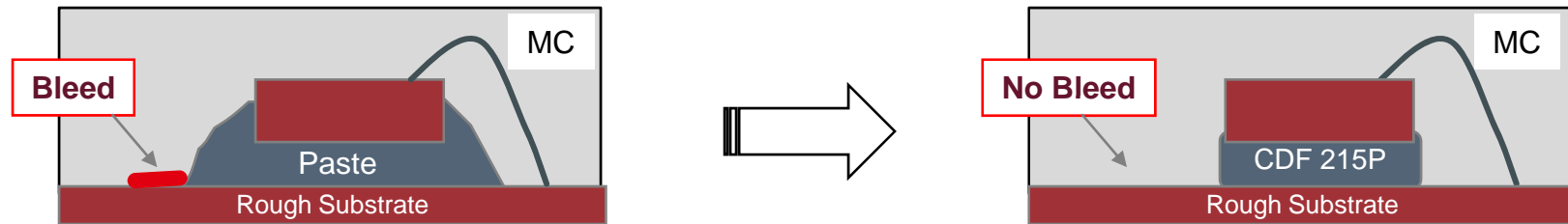


Lower crosslinking density  
High toughness

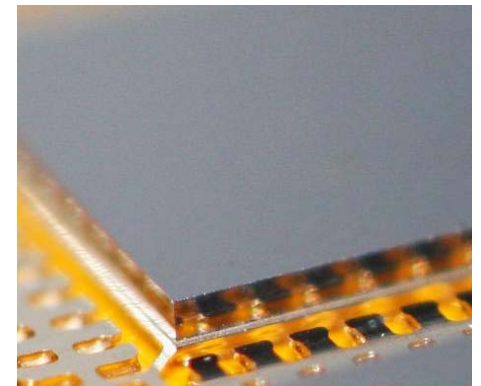
Better adhesion  
Better MSL performance

# Material Benefits of cDAF

## Potential for Zero Delam applications

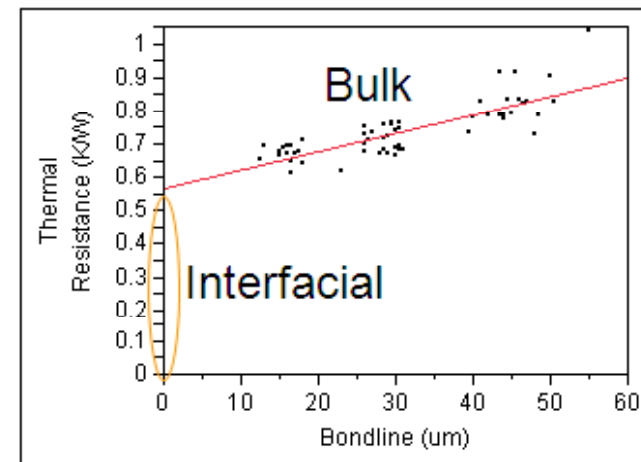
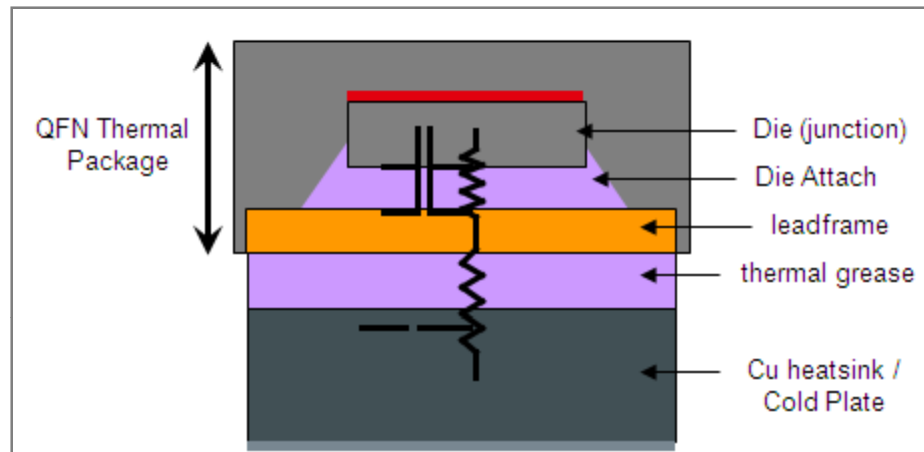


- Conductive films do not bleed and do not have a fillet, so the adhesion of MC to LF is stronger – regardless of LF finish: smooth or rough.
- CDAF also has minimal out-gassing, which ensures clean WB bond pads & die top –
  - wirebonding or MC-die top delamination not observed



# Thermal & Electrical for cDAF

## Stable In-Package performance



- Thermal Conductivity [W/mK] is an intrinsic material property
- Thermal Resistance,  $R_{th}$  [K/W], is a geometry dependant value that allows us to better compare materials in a functional package
  - 70 – 90% of the  $R_{th}$  is due to the interfaces and is not captured in thermal conductivity values

Conductive films are designed to have optimal performance in the z-axis direction

# Portfolio of CDAF Products

## Property table for film and paste

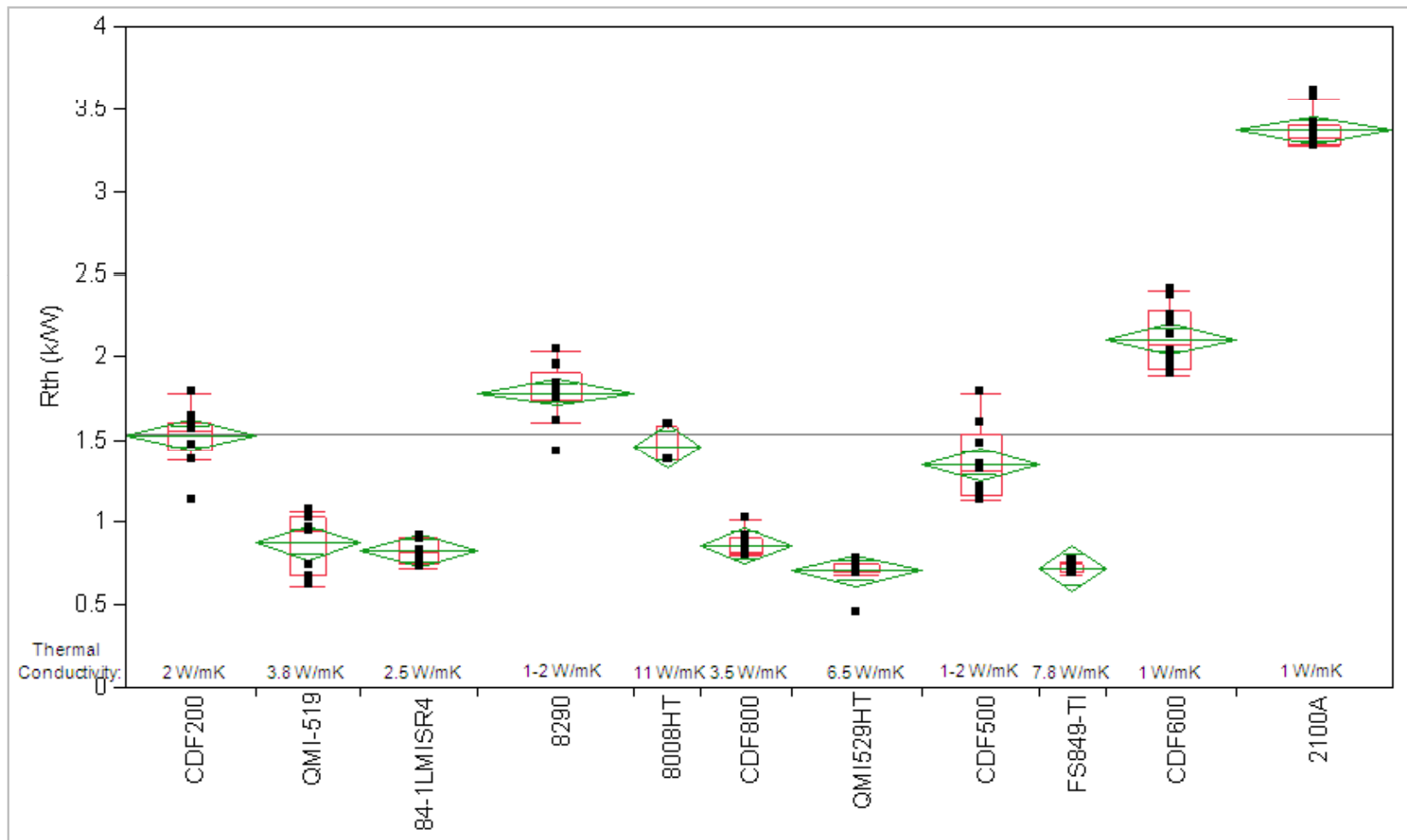
	unit	CDF 200P	QMI519	84-1LMI SR4	8290	8008HT	CDF 800P	QMI529HT	CDF 500P	FS849-TI	CDF 600	2100A
<b>Material Property</b>												
Volume Resistivity	ohm-cm	0.0014	0.0001	0.0002	0.008	0.00006	0.0003	0.00004	0.0002	0.00002	0.0008	0.05
Thermal conductivity	W/mK	2	3.8	2.5	1.6	11	3.5	6.5	1 - 2	7.8	1	1.35
CTE alpha1	ppm/C	48	40	40	81	37	40	53	60	44	75	65
CTE alpha 2	ppm/C	120	140	150	181	62	118	156	245	155	320	200
Tg	°C	15	75	120	38	264	11	3	10	211	"-5	60
Modulus @ 25C	Mpa	5,400	5,300	3,930	3,034	6,659	7,100	3,300	11,300	7,800	3,000	3,200
Modulus @ 250C	Mpa	1,000	287	303	117	2,450	900	-	130	1,070	40	230
<b>Performance</b>												
HDSS (260°C) on Ag	kg/mm^2	1.3	0.8	0.2	0.6	0.7	1.0	0.5	0.7	0.5	0.7	0.4
Room Temp DSS on PPF	kg/mm^2	2.14	4.9	3.0	5.0	-	> 2.0	-	-	-	-	-
Room Temp DSS on Ag	kg/mm^2	3.02	4.8	2.3	5.1	1.5	> 2.0	2.2	-	-	-	-
Room Temp DSS on Cu	kg/mm^2	3.17	1.8	1.2	2.5	1.5	> 2.0	-	-	-	-	-
Failure Mode		Cohesive	Cohesive	Cohesive	Cohesive	-	Cohesive	Cohesive	Cohesive	-	Cohesive	Cohesive
Thermal Resistance, Rth	K/W	1.5	1.3	0.83	1.8	1.5	0.81	0.77	1.5	0.72	2.1	2.3
RDson	ohm	0.075	0.044	0.033	n/a	0.067	0.032	0.042	0.055	0.038	n/a	n/a
RDson Shift (500 TC)	%	2.2	n/a	10.0	n/a	n/a	5.7	42	n/a	28.0	n/a	n/a
RDson Shift (1000 TC)	%	6.6	n/a	15.6	n/a	n/a	6.4	42	n/a	28.8	n/a	n/a
JEDEC MSL 260°C (on 7x7mm PPF QFN with 2.5x2.5x0.33 die)	MSL level	1	MSL1 capable for small die	3	MSL1 capable for small die	3	1	MSL1 capable for small die	1	MSL1 capable for small die	2 (PBGA)	2 (PBGA)
JEDEC MSL 260°C (on 7x7mm PPF QFN with 5x5x0.36 die)	MSL level	2	-	-	-	-	2	-	1	3	2 (PBGA)	2 (PBGA)
<b>Processing</b>												
Cure	profile	30 min ramp to 200C + 1hr soak @ 200C	30 min. ramp + hold 60 min @ 100°C + 15 min ramp + hold 60 min @ 200°C.	30 min ramp to 175C + 1hr soak @ 175C	30 min ramp to 175C + 15min soak @ 175C	20 seconds @ 280°C	30 min ramp to 200C + 1hr soak @ 200C	30 min ramp to 185C + 30 min soak @ 185C	30 min ramp to 200C + 1hr soak @ 200C	30 min ramp to 175C + 30 min soak @ 175C	30 min ramp + 100C/30min + 30 min ramp + 170C/1hr	30 min ramp to 175C + 15min soak @ 175C



# Thermal Resistance

## Comparison of paste and film materials

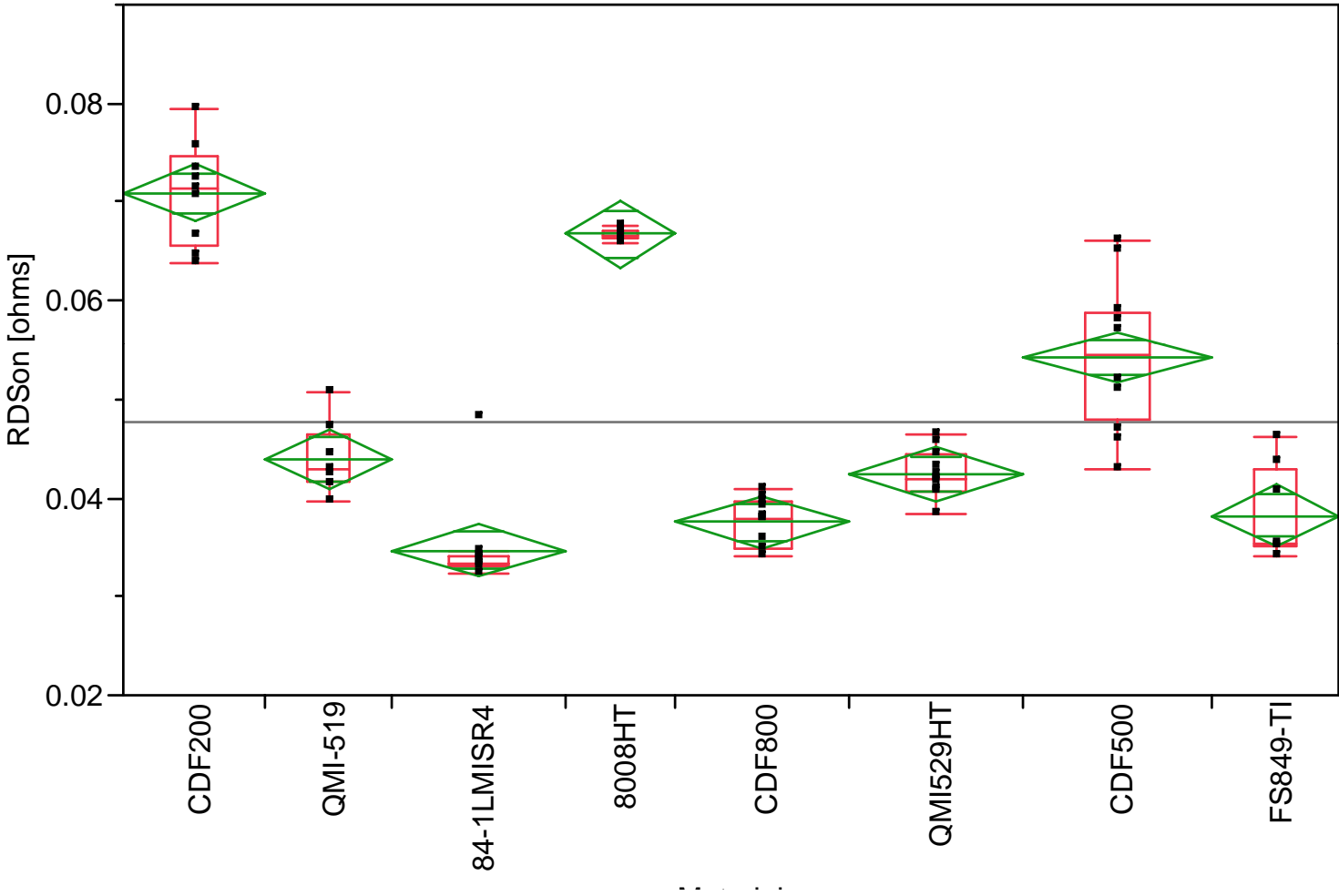
2.5x2.5x0.36mm<sup>2</sup> Si-back die  
QFN 7x7mm, PPF (pad 5.8x5.8mm)  
30min RAMP + 200°C 1hr cure



# RDSon

## In package performance

2.0x2.9x0.18mm; TiNiAg-back die  
TO-220, Cu pad



# Conductive Die attach Film

## Laser Dicing

	Blade Dicing	Laser Dicing
Process method	Mechanical cutting	Surface absorption laser process (melting, evaporation)
Water (cooling / cleaning)	Required	Required for cleaning only
Chipping?	Yes	Less chipping
Debris generation?	Yes	Yes
T-shape and round shape dicing	Not possible	Possible in certain cases
Ultra-thin wafer dicing possible?	Limited	Possible
Kerf Width	15 to 25 $\mu\text{m}$	Less than 15 $\mu\text{m}$
Processing speed	5 to 10 mm/s	225 mm/s

CDAF is compatible with both blade and laser dicing on Si or GaAs wafers

# Advantages of Control Flow

## CDAF – Material Advantages

- **Thin wafer handling with precut format**
  - Excellent electrical conductivity, very low RDSon shift (<10%)
  - Thinner package and smaller footprint (higher density packaging)
  - Potentially eliminate wafer backside metallization
  - In multi-die packages allow shorter die-to-die wirebonds for faster speeds.
- **Consistent bondline thickness and controlled flow**
  - No die tilt,
  - Design flexibility from tight clearance between die and die pad
- **Clean dry process**
  - No dispensing, printing/B-staging necessary
  - No bleed (even on rough LFs), no fillet, uniform bondline, no kerf creep
- **Reliability performance**
  - Higher reliability performance (MSL1) on multiple substrates (PPF, Ag Spot, Cu) and various wafer back metallization (Si, Au, Ag)
  - Achieve better efficiency, reduce yield loss: Efficient and robust process
- **Cost Savings**
  - Higher density leadframes, shorter Au wires and less mold compound usage

# Thank you!

# Henkel Electronics Adhesives Headquarters

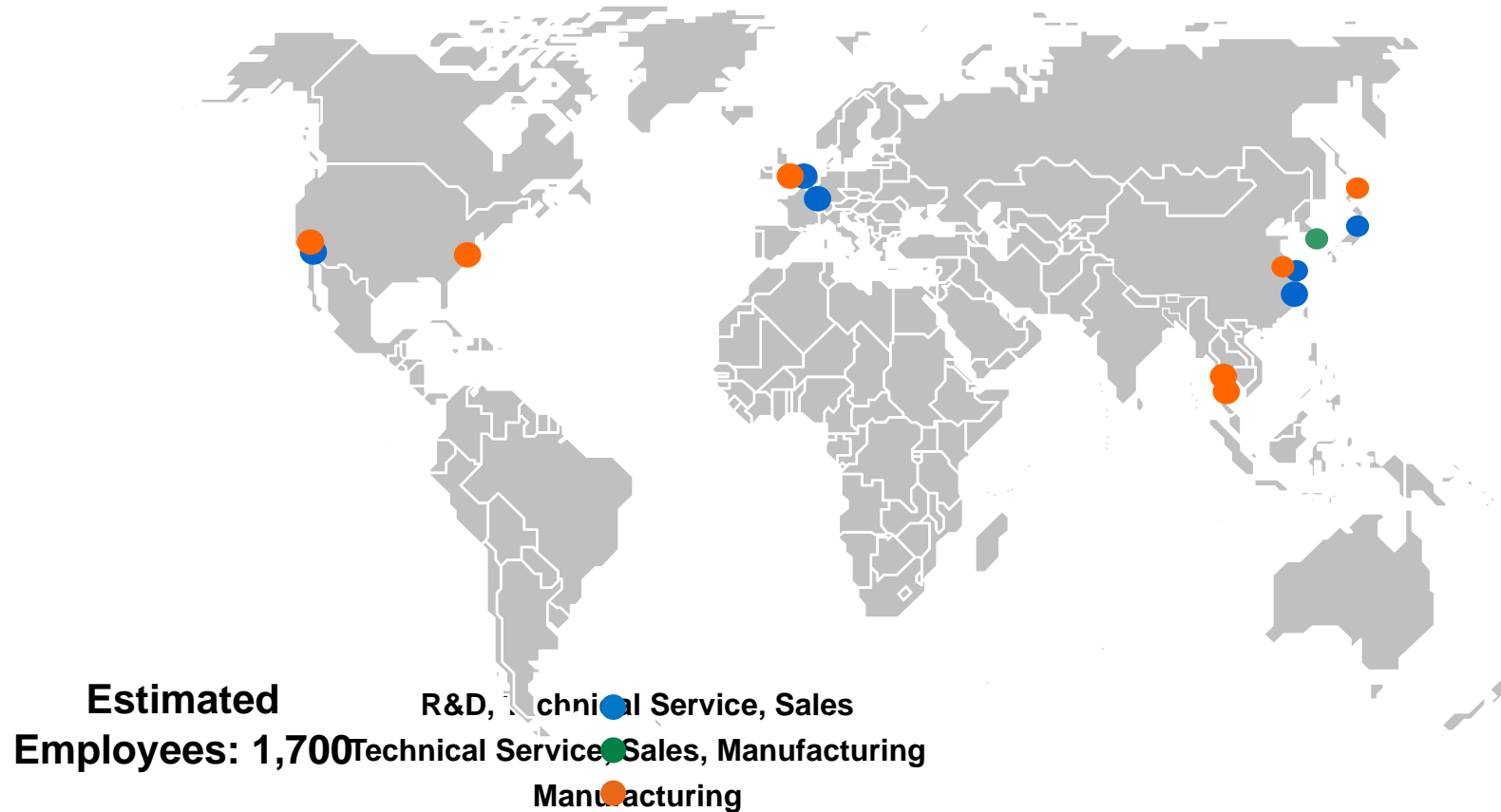
Irvine, California



**Alan Syzdek**  
Corp Sr. Vice President

# Serving our Customers Worldwide

## Adhesive Electronics Global End to End Business



- Henkel has a global presence with a footprint in every geography.
- Globally aligned infrastructure to serve our customers locally.